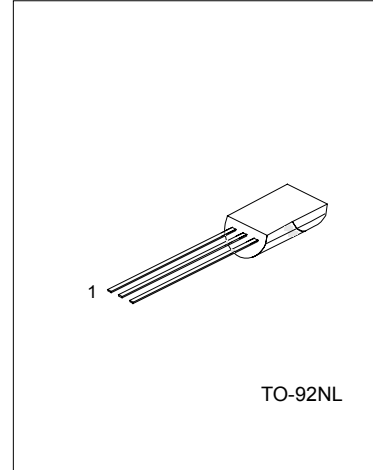


LOW FREQUENCY POWER AMPLIFIER

FEATURES

- *Low frequency power amplifier
- *Complement to 2SD468



1:EMITTER 2:COLLECTOR 3:BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CB0}	-25	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _c	-1	A
Collector Peak Current	I _{c(peak)}	-1.5	A
Collector Power Dissipation	P _c	0.9	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

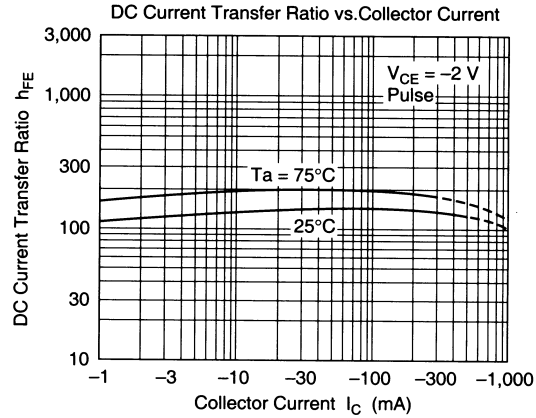
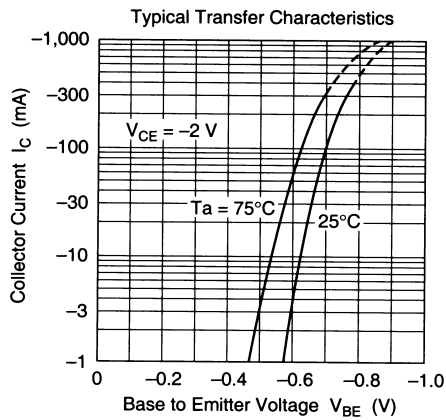
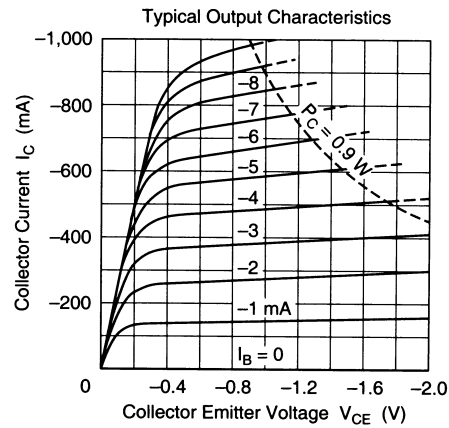
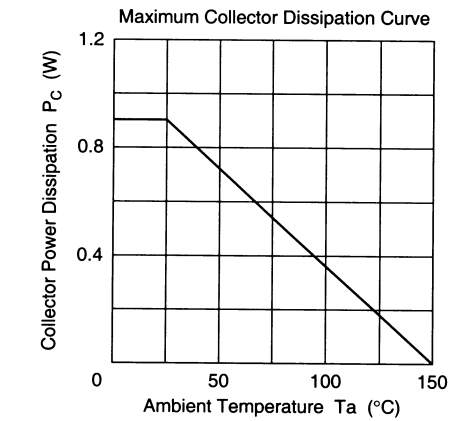
ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector to base breakdown voltage	V _{(BR)CBO}	I _c =-10μA, I _E =0	-25			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _c =-1mA, R _{BE} =∞	-20			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _c				

CLASSIFICATION OF h_{FE}

RANK	B	C
RANGE	85 - 170	120 - 240

TYPICAL PERFORMANCE CHARACTERISTICS



UTC2SB562 PNP EPITAXIAL SILICON TRANSISTOR

